



PATENT
005702-20035 (81788.0020)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Shota KITAMURA, et al.

Serial No: 09/392,865

Filed: September 9, 1999

For: NON-VOLATILE
SEMICONDUCTOR MEMORY
DEVICE AND ITS
MANUFACTURING METHOD

Art Unit: 2811

Examiner: Tran, T.

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AMENDMENT

Box Non-Fee Amendment
Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Office Action dated June 22, 2001, please amend the
above-identified application as follows:

IN THE CLAIMS:

Rewrite claim 16 as follows:

16. (Amended) A nonvolatile semiconductor memory device comprising:

a semiconductor substrate;

memory transistors formed on said semiconductor substrate to perform

nonvolatile storage of an electric charge in accordance with data, each of said

memory transistors being an electrically rewritable memory transistor including a

floating gate formed over said semiconductor substrate via a first gate insulating

film and a control gate formed over said floating gate via a second gate insulating

film;